

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claim 1 (original): A surface acoustic wave device comprising:
first and second double-mode surface acoustic wave resonator filters connected in parallel to each other, each of said first and second double-mode surface acoustic wave resonator filters including a piezoelectric substrate, IDT electrodes and grating reflectors disposed on the piezoelectric substrate; wherein
the first double-mode surface acoustic wave resonator filter has resonance frequencies f_{1L} and f_{1H} , where $f_{1L} < f_{1H}$;
the second double-mode surface acoustic wave resonator filter has resonance frequencies f_{2L} and f_{2H} , where $f_{2L} < f_{2H}$;
 $f_{1H} = f_{2L}$; and
an energy transmittance of the reflectors in at least one of the first and the second double-mode surface acoustic wave resonator filters ranges from about 12% to about 28%.

Claim 2 (original): The surface acoustic wave device according to Claim 1, wherein a fractional bandwidth that is a ratio of a passband to the center frequency of the passband ranges from about 0.18% to about 0.22%.

Claim 3 (original): The surface acoustic wave device according to Claim 1, wherein the first double-mode surface acoustic wave resonator filter and the second double-mode surface acoustic wave resonator filter are disposed on the same piezoelectric substrate.

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Claim 4 (original): The surface acoustic wave device according to Claim 1, wherein the piezoelectric substrate is a quartz substrate.

Claim 5 (original): The surface acoustic wave device according to Claim 1, wherein the piezoelectric substrate is an LiTaO_3 substrate.

Claim 6 (original): The surface acoustic wave device according to Claim 1, wherein the piezoelectric substrate is an LiNbO_3 substrate.

Claim 7 (currently amended): The surface acoustic wave device according to Claim 1, wherein the IDT electrodes and the grating reflectors are made of a thin metal film having a thickness of about 3% of a ~~thickness of the piezoelectric substrate~~ wavelength of a selected surface acoustic wave.

Claim 8 (currently amended): The surface acoustic wave device according to Claim 47, wherein the thin metal film primarily includes Al.

Claim 9 (original): A surface acoustic wave device comprising:
first and second double-mode surface acoustic wave resonator filters connected in parallel to each other, each of said first and second double-mode surface acoustic wave resonator filters including a piezoelectric substrate, IDT electrodes disposed on the piezoelectric substrate, and grating reflectors on both sides of a region where the IDT electrodes are disposed in the surface acoustic wave propagation direction; wherein

the first double-mode surface acoustic wave resonator filter has resonance frequencies f_{1L} and f_{1H} , where $f_{1L} < f_{1H}$;

the second double-mode surface acoustic wave resonator filter has resonance frequencies f_{2L} and f_{2H} , where $f_{2L} < f_{2H}$;

$f_{1H} = f_{2L}$; and

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a Q factor of a resonance mode of one of the first and the second double-mode surface acoustic wave resonator filter is less than a Q factor of a resonance mode of the other double-mode surface acoustic wave resonator filter.

Claim 10 (original): The surface acoustic wave device according to Claim 9, wherein a fractional bandwidth that is a ratio of a passband to the center frequency of the passband ranges from 0.18% to 0.22%.

Claim 11 (original): The surface acoustic wave device according to Claim 9, wherein the first double-mode surface acoustic wave resonator filter and the second double-mode surface acoustic wave resonator filter are disposed on the same piezoelectric substrate.

Claim 12 (original): The surface acoustic wave device according to Claim 9, wherein the piezoelectric substrate is a quartz substrate.

Claim 13 (original): The surface acoustic wave device according to Claim 9, wherein the piezoelectric substrate is an LiTaO_3 substrate.

Claim 14 (original): The surface acoustic wave device according to Claim 9, wherein the piezoelectric substrate is an LiNbO_3 substrate.

Claim 15 (currently amended): The surface acoustic wave device according to Claim 9, wherein the IDT electrodes and the grating reflectors are made of a thin metal film having a thickness of about 3% of a ~~thickness of the piezoelectric substrate~~ wavelength of a selected surface acoustic wave.

Claim 16 (currently amended): The surface acoustic wave device according to Claim ~~9~~15, wherein the thin metal film primarily includes Al.